

L4 ANSWER 1 OF 3 CAPLUS COPYRIGHT 2005 ACS on STN  
 AN 2000:819209 CAPLUS  
 DN 133:351330  
 ED Entered STN: 22 Nov 2000  
 TI Microporous insulating materials with excellent heat resistance and laminates therefrom  
 IN Yao, Shigeru; Oya, Nobuo  
 PA Ube Industries, Ltd., Japan  
 SO Jpn. Kokai Tokkyo Koho, 9 pp.  
 CODEN: JKXXAF  
 DT Patent  
 LA Japanese  
 IC ICM C08J009-28  
 ICS B32B005-18; H01B003-30; H01B005-14; H01B017-56; H01B017-64  
 CC 38-3 (Plastics Fabrication and Uses)  
 Section cross-reference(s): 76  
 FAN. CNT 3

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2000319442	A2	20001121	JP 1999-132755	19990513 <--
	US 2003129379	A1	20030710	US 2000-539929	20000331
	US 2004166297	A1	20040826	US 2004-785413	20040225
	US 2004241419	A1	20041202	US 2004-784982	20040225
PRAI	JP 1999-116178	A	19990423		
	JP 1999-132755	A	19990513		
	JP 1999-337445	A	19991129		
	US 2000-539929	B1	20000331		

# CLASS

	PATENT NO.	CLASS	PATENT FAMILY CLASSIFICATION CODES
	JP 2000319442	ICM	C08J009-28
		ICS	B32B005-18; H01B003-30; H01B005-14; H01B017-56; H01B017-64
	US 2003129379	NCL	428/308.400; 428/315.700
		ECLA	B32B027/06; C08J005/18+L79/08; H05K001/03C2E
	US 2004166297	NCL	428/209.000; 428/901.000
		ECLA	B32B027/06; C08J005/18+L79/08; H05K001/03C2E
	US 2004241419	NCL	428/319.100; 428/315.700; 428/315.500; 428/317.100
		ECLA	B32B027/06; C08J005/18+L79/08; H05K001/03C2E
AB	The materials, useful for circuit boards, comprise heat-resistant polymer films with continuous micropore structures with porosity 15-80%. Thus, a microporous polyimide film manufactured from 3,3',4,4'-biphenyltetracarboxylic dianhydride and 4,4'-diaminodiphenyl ether showed thickness 40 µm, average pore size 0.5 µm, and porosity 60%.		
ST	insulator microporous polyimide film circuit board; heat resistance polyimide adhesive copper laminate		
IT	Electric insulators Printed circuit boards (elec. insulating microporous films with good heat resistance for printed circuit boards)		
IT	Polyimides, uses RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (elec. insulating microporous films with good heat resistance for printed circuit boards)		
IT	Laminated plastics, uses RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses) (elec. insulating microporous films with good heat resistance for printed circuit boards)		
IT	Polysiloxanes, uses		

Polysiloxanes, uses  
 Polysiloxanes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (epoxy-polyimide-, heat-resistant adhesive; elec. insulating  
 microporous films with good heat resistance for printed circuit boards)

IT Polyimides, uses  
 Polyimides, uses  
 Polyimides, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (epoxy-siloxane-, heat-resistant adhesive; elec. insulating microporous  
 films with good heat resistance for printed circuit boards)

IT Adhesives  
 (heat-resistant; elec. insulating microporous films with good heat  
 resistance for printed circuit boards)

IT Plastic films  
 (microporous; elec. insulating microporous films with good heat  
 resistance for printed circuit boards)

IT Polyimides, uses  
 Polyimides, uses  
 RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or  
 engineered material use); PREP (Preparation); USES (Uses)  
 (polyether-; elec. insulating microporous films with good heat  
 resistance for printed circuit boards)

IT Polyethers, uses  
 Polyethers, uses  
 RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or  
 engineered material use); PREP (Preparation); USES (Uses)  
 (polyimide-; elec. insulating microporous films with good heat  
 resistance for printed circuit boards)

IT Epoxy resins, uses  
 Epoxy resins, uses  
 Epoxy resins, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (polyimide-siloxane-, heat-resistant adhesive; elec. insulating  
 microporous films with good heat resistance for printed circuit boards)

IT 26298-81-7P, 3,3',4,4'-Biphenyltetracarboxylic dianhydride-4,4'-  
 diaminodiphenyl ether copolymer 26615-45-2P, 3,3',4,4'-  
 Biphenyltetracarboxylic dianhydride-4,4'-diaminodiphenyl ether copolymer,  
 sru 29319-22-0P, 3,3',4,4'-Biphenyltetracarboxylic dianhydride-p-  
 phenylenediamine copolymer 32197-39-0P 74049-11-9P,  
 3,3',4,4'-Biphenyltetracarboxylic dianhydride-4,4'-diaminodiphenyl  
 ether-p-phenylenediamine copolymer  
 RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or  
 engineered material use); PREP (Preparation); USES (Uses)  
 (elec. insulating microporous films with good heat resistance for  
 printed circuit boards)

IT 7440-50-8, Copper, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (foil; elec. insulating microporous films with good heat resistance for  
 printed circuit boards)

RN 26298-81-7P  
 RN 26615-45-2P  
 RN 29319-22-0P  
 RN 32197-39-0P  
 RN 74049-11-9P  
 RN 7440-50-8

L4 ANSWER 2 OF 3 WPIX COPYRIGHT 2005 THE THOMSON CORP on STN  
 AN 2001-075354 [09] WPIX  
 CR 2001-141447 [15]; 2002-002004 [01]  
 DNN N2001-057253 DNC C2001-022083  
 TI Porous insulating material useful in high frequency electronic components,  
 comprises high heat-resistant resin film having porous structure with fine

continuous pores and specified porosity.

DC A26 A85 L03 P73 V01 X12 X16

IN ASANO, Y; FUKUNAGA, K; KAWABATA, K; KINOUCHI, M; OHYA, S; YAO, S

PA (UBEI) UBE IND LTD; (ASAN-I) ASANO Y; (FUKU-I) FUKUNAGA K; (KAWA-I) KAWABATA K; (KINO-I) KINOUCHI M; (OHYA-I) OHYA S; (YAOS-I) YAO S

CYC 2

PI JP 2000319442 A 20001121 (200109)\* 9 C08J009-28 <--  
 US 2003129379 A1 20030710 (200347) B32B003-26  
 US 2004166297 A1 20040826 (200457) B32B003-00  
 US 2004241419 A1 20041202 (200481) B32B003-26

ADT JP 2000319442 A JP 1999-132755 19990513; US 2003129379 A1 US 2000-539929 20000331; US 2004166297 A1 Cont of US 2000-539929 20000331, US 2004-785413 20040225; US 2004241419 A1 Div ex US 2000-539929 20000331, US 2004-784982 20040225

PRAI JP 1999-132755 19990513; JP 1999-116178 19990423;  
 JP 1999-337445 19991129

IC ICM B32B003-00; B32B003-26; C08J009-28  
 ICS B32B005-18; H01B003-30; H01B005-14; H01B017-56; H01B017-64

AB JP2000319442 A UPAB: 20041216  
 NOVELTY - The porous insulating material (1) comprises high heat-resistant resin film (3), such as polyimide film, having porous structure with fine continuous pores (2). The film has a porosity of 15-80%.  
 DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for the porous insulating material laminate.  
 USE - As electrical insulating material in high frequency electronic components, such as portable mobile communications e.g. Vehicle telephone, digital portable telephone and satellite communication devices.  
 ADVANTAGE - The material has excellent electrical property (low dielectric constant) and excellent heat-resistance. The porous insulating material has high adhesive property with metals and metallic foils, as substrates.  
 DESCRIPTION OF DRAWING(S) - The figure shows cross-sectional view of porous insulating material such as porous polyimide film.  
 Porous polyimide film 1  
 Continuous pore 2  
 High heat-resistant film 3  
 Dwg. 1/7

FS CPI EPI GMPI

FA AB; GI

MC CPI: A12-E01  
 EPI: X12-D02A1; X12-E02B; X12-E03C

L4 ANSWER 3 OF 3 JAPIO (C) 2005 JPO on STN

AN 2000-319442 JAPIO

TI POROUS INSULATION MATERIAL AND LAMINATE THEREOF

IN YAO SHIGERU; OYA NOBUO

PA UBE IND LTD

PI JP 2000319442 A 20001121 Heisei

AI JP 1999-132755 (JP11132755 Heisei) 19990513

PRAI JP 1999-132755 19990513

SO PATENT ABSTRACTS OF JAPAN (CD-ROM), Unexamined Applications, Vol. 2000

IC ICM C08J009-28  
 ICS B32B005-18; H01B003-30; H01B005-14; H01B017-56; H01B017-64

AB PROBLEM TO BE SOLVED: To obtain a porous material having heat resistance, a low permittivity, a low dielectric loss, and excellent insulation properties by using a highly heat-resistant resin film having a porous structure having fine continuous pores and a specified porosity.  
 SOLUTION: The porous insulation material has a permittivity of at most 2.5. The highly heat-resistant resin film has a porosity of 15-80% and is desirably a polyimide film. The porous polyimide film is obtained, for example, by the following method. A casting of a polyimide precursor solution is brought into contact with a coagulation medium through an agent for regulating the rate of solvent displacement to form a porous

deposit of the precursor, and the porous polyimide precursor film is thermally or chemically imidized. A heat- resistant adhesive layer is laid on at least either surface of the film, and a protective film is formed on the adhesive layer to form a laminate. In use, the laminate is stripped of the protective film, and a conductive metallic foil for an electronic circuit is laid on the protective film to easily obtain a circuit board.  
COPYRIGHT: (C)2000,JPO

=>